

P-Channel MOSFET Transistor

2SJ79 / J79

200V / 0.5A

DATASHEET

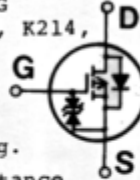
OEM – Hitachi

Source: Hitachi Databook Power Mosfet Data 4/83

2SJ76, 2SJ77, 2SJ78, 2SJ79

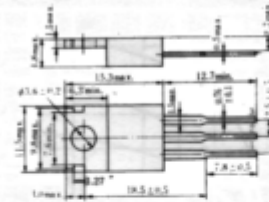
SILICON P-CHANNEL MOS FET

HIGH FREQUENCY AND LOW FREQUENCY POWER AMPLIFIER, HIGH SPEED SWITCHING
Complementary Pair with 2SK213, K214, K215, K216



Features;

- Suitable for Direct Mounting.
- High Forward Transfer Admittance.
- Excellent Frequency Response.
- Enhancement-Mode.



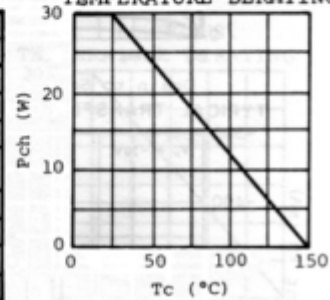
(Dimensions in mm)
(JEDEC TO-220AB)

1. Gate
2. Source (Flange)
3. Drain

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Ratings				Unit
		J76	J77	J78	J79	
Drain-Source Voltage	V_{DSX}	-140	-160	-180	-200	V
Gate-Source Voltage	V_{GSS}	±15				V
Drain Current	I_D	-500				mA
Body-Drain Diode Reverse Drain Current	I_{DR}	-500				mA
Channel Dissipation	Pch	1.75				W
	Pch*	30				W
Channel Temperature	Tch	150				°C
Storage Temperature	Tstg	-45 ~ +150				°C

POWER VS. TEMPERATURE DERATING



*Value at Tc=25°C

■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	J76	$V_{GS}=2V, I_D=-1mA$	-140	-	-	V
	J77		-160	-	-	V
	J78		-180	-	-	V
	J79		-200	-	-	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G=\pm 10\mu A, V_{DS}=0$	±15	-	-	V
Gate-Source Voltage	$V_{GS(on)}$	$I_D=-10mA, V_{DS}=-10V^*$	-0.2	-	-1.5	V
Drain-Source Saturation Voltage	$V_{DS(sat)}$	$I_D=-10mA, V_{GD}=0^*$	-	-	-2.0	V
Forward Transfer Admittance	$ y_{fs} $	$I_D=-10mA, V_{DS}=-20V^*$	-	35	-	mS
Input Capacitance	Ciss	$V_{DS}=-10V, I_D=-10mA, f=1MHz$	-	120	-	pF
Reverse Transfer Capacitance	Crss	$f=1MHz$	-	4.8	-	pF

*Pulse Test

2SJ76,2SJ77,2SJ78,2SJ79

